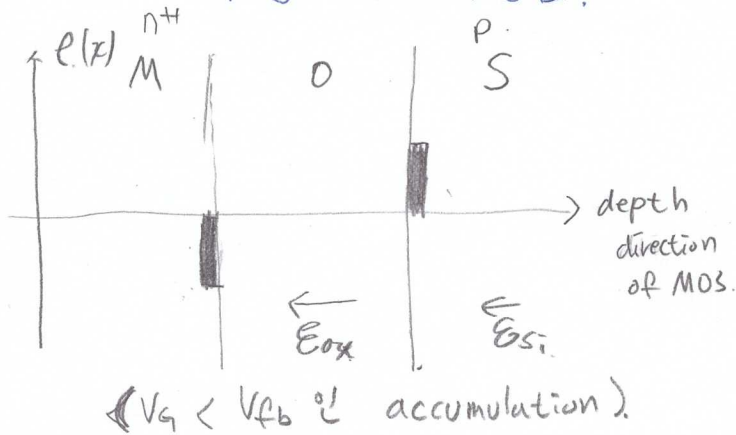
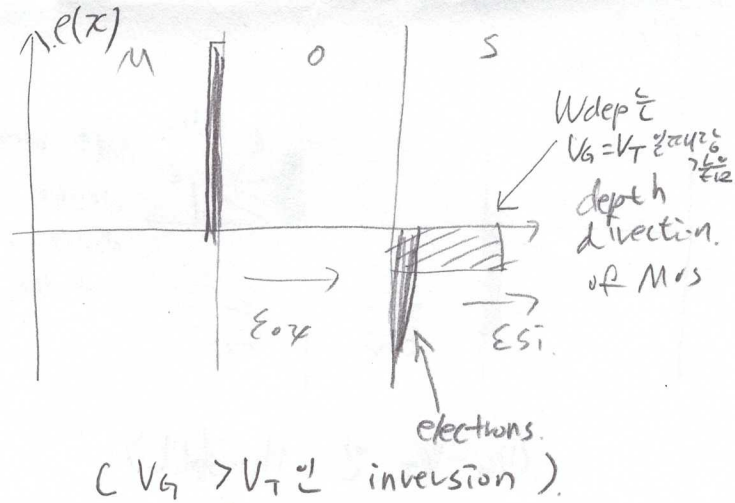
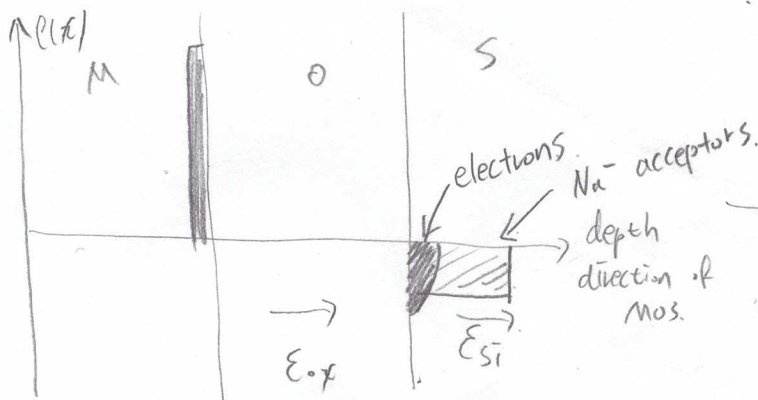
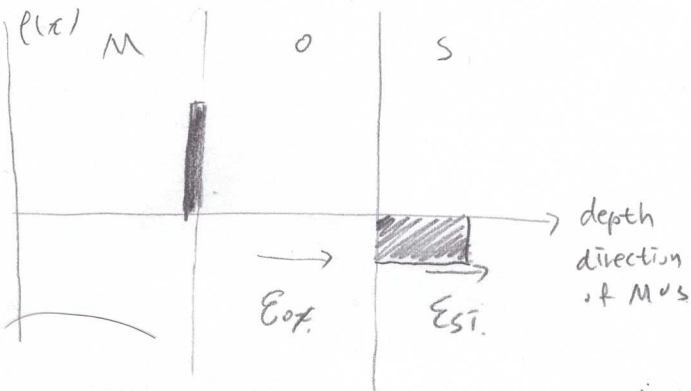


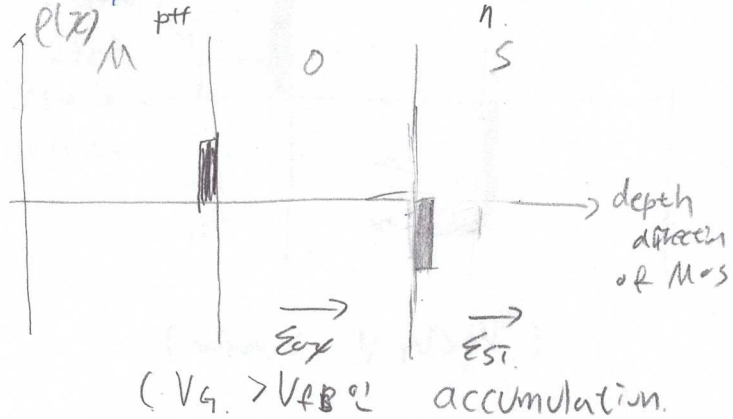
1. 상기 MOS Capacitor 구조에서 gate 전압 조건에 따른 substrate 상태가 accumulation, depletion, threshold, inversion 일때의 charge distribution을 각각 도식해 보시오. 단, substrate는 p-type doping 조건을 가정함.



$V_G = V_{fb}$ 일때 flat band라.
Charge distribution X.



2. 1번 질문이 대해 substrate doping 조건이 n-type 인 경우에 다시 도식해 보시오.



$V_G = V_{fb}$ 일때 flat band라.
Charge distribution X.

